

Appl. No. 09/879,335

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22. (amended) A capacitor forming method comprising:
- forming a barrier layer to V_t shift inducing material over a substrate, the substrate including an electronic device;
 - forming an insulation layer over the barrier layer;
 - forming an opening into at least the insulation layer;
 - forming a high K capacitor dielectric layer at least within the opening; and
 - providing V_t shift inducing material over the barrier layer, the barrier layer retarding movement of the V_t shift inducing material into the electronic device.

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